

AMENDMENT TO THE SPECIFICATION

Please replace paragraph [0036] of the specification with the following amended paragraph [0036]:

[0036] After removal of the mask, the entire unmasked surface may be subjected to another dose of nitrogen, such as by exposing the structure to a nitrogen containing gas such as ammonia (NH₃), as shown in FIG. 6. This exposure forms a thin nitride (Si₃N₄) film 610 on exposed substrate, introduces additional nitride on layer 320 and introduces a second amount of nitrogen into the dielectric area 310. During the time in which the structure is exposed to the gas, an annealing process is carried out. The annealing process may take place using a conventional furnace process (i.e., furnace nitridation) or a rapid thermal process (i.e., rapid thermal nitridation). The annealing conditions may include a temperature within the range of about 400°C. to 800°C., a pressure of 10 torr to 1 atmosphere, and an annealing time of 15 seconds to 120 minutes depending upon the type of process. The duration, temperature and pressure may be varied to increase or decrease the amount of nitrogen introduced. By way of example and not limitation, a nitridation step according to the conditions described above may add nitrogen in the range of 1×10^{13} to 1×10^{15} ~~atoms/cm³~~ atoms/cm² (e.g., 1×10^{14} to 1×10^{15} ~~atoms/cm³~~ atoms/cm²). The thickness of nitride file 610 may be approximately 10 to 50 Å. However, other levels of nitrogen concentration and other film thicknesses may be achieved.

Please replace paragraph [[0047] of the specification with the following amended paragraph [0047]:

[0047] Optionally, nitrogen may also be implanted in n-wells (e.g., well 1150) for p-FET regions. Referring now to FIG. 12, mask 1230 is formed to mask those areas of the structure which are to become nFET regions 1140, and expose those portions of the structure which are to become pFET regions 1150. Alternatively, as nFETs benefit from high nitrogen concentrations, mask 1230 may be omitted. Nitrogen may be implanted through sacrificial oxide layer 1110 into underlying unmasked areas. Sacrificial oxide layer 1110 attenuates the implantation so that the majority of implanted nitrogen atoms

form a nitrogen enriched area at the well surfaces 1150. For pFETs, a low dose of implanted nitrogen may yield approximately 1×10^{13} to 1×10^{15} ~~atoms/cm³~~ atoms/cm² in the well. After implantation, the mask 1230, if any, is stripped using well known techniques. Optionally, a rapid thermal anneal (e.g., 1050° C. for 30 seconds) may be performed to diffuse implanted nitrogen.